

12-36GHz Frequency Multiplier

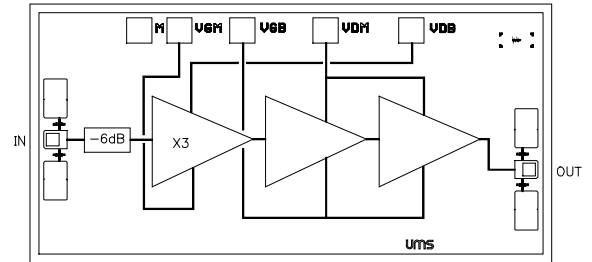
GaAs Monolithic Microwave IC

Description

The CHX1094 is a cascaded frequency multiplier by 3 monolithic circuit.

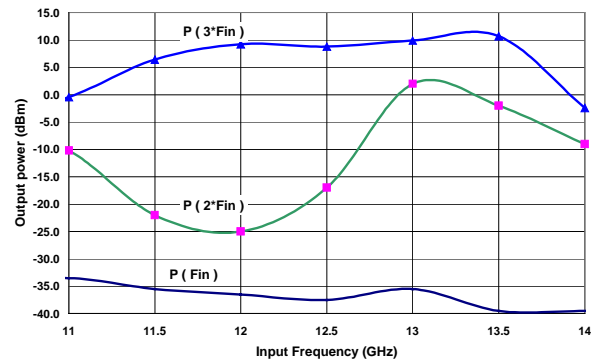
It is designed for a wide range of applications, from military to commercial communication systems. The backside of the chip is both RF and DC grounds. This helps simplify the assembly process.

The circuit is manufactured with a P-HEMT process, 0.25µm gate length, via holes through the substrate, air bridges and electron beam gate lithography.



Main Features

- Broadband performances : 12-13.5GHz
- 10dBm output power for +14dBm input power
- DC bias : Vd=3.Volt @Id=60mA
- Chip size : 2.07 x 1.03 x 0.10 mm



typical measurement

Main Characteristics

Tamb. = 25°C

| Symbol | Parameter | Min | Typ | Max | Unit |
|--------|---------------------------|-----|-----|------|------|
| Fin | Input frequency range | 12 | | 13.5 | GHz |
| Fout | Output frequency range | 36 | | 40.5 | GHz |
| Pin | Input power | | 14 | | dBm |
| Pout | Output power @ Pin= 14dBm | | 10 | | dBm |

ESD Protection : Electrostatic discharge sensitive device. Observe handling precautions !

Electrical Characteristics

Tamb = +25°C, Vgm = -1.5V , Vgb = -0.2V.

| Symbol | Parameter | Min | Typ | Max | Typ | Unit |
|---------|---|-----|-----|-------|-------|------|
| Fin | Input frequency range | 12 | | 13.5 | 14 | GHz |
| Fout | Output frequency range | 36 | | 40.5 | 42 | GHz |
| Pin | Input power | 12 | 14 | 16 | 16 | dBm |
| Pout | Output power @ Pin=14dBm | 8 | 10 | | 5 | dBm |
| H3/H2 | 2 nd Harmonic rejection (Pin ≤ 14dBm) | 8 | 10 | | 5 | dBc |
| H3/H1 | Fund. rejection (Pin ≤ 14dBm) | 30 | | | 35 | dBc |
| VSWRin | Input VSWR | | | 2:1 | 2:1 | |
| VSWRout | Output VSWR | | | 2.5:1 | 2.5:1 | |
| Vd | DC voltage | 2.5 | | 3.5 | 4 | V |
| Id | Bias current | | 60 | 80 | 80 | mA |

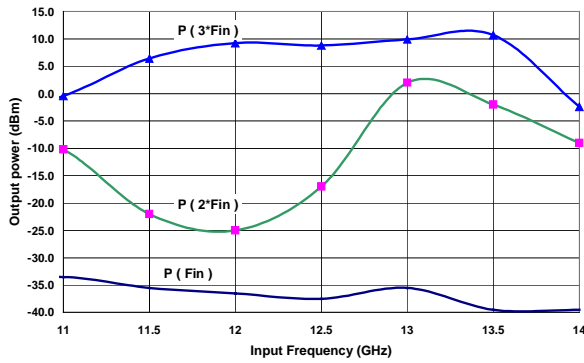
Absolute Maximum Ratings

Tamb. = 25°C (1)

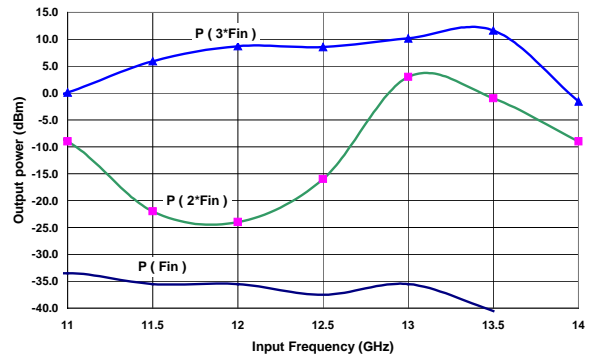
| Symbol | Parameter | Values | Unit |
|--------|-----------------------------|-------------|------|
| Vd | Drain bias voltage | 4.5 | V |
| Id | Drain bias current | 120 | mA |
| Vg | Gate bias voltage | -2 to +0.4 | V |
| Ta | Operating temperature range | -40 to +85 | °C |
| Tstg | Storage temperature range | -55 to +155 | °C |

(1) Operation above anyone of these parameters may cause permanent damage of this device.

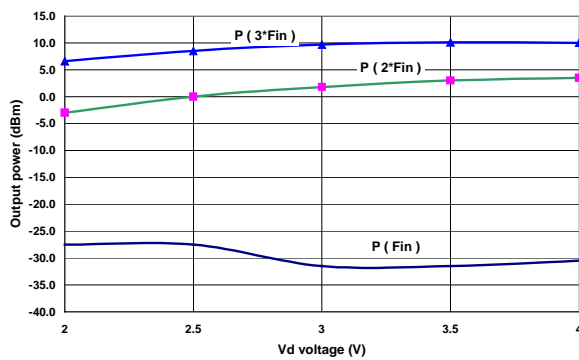
Typical on Jig Measurements.



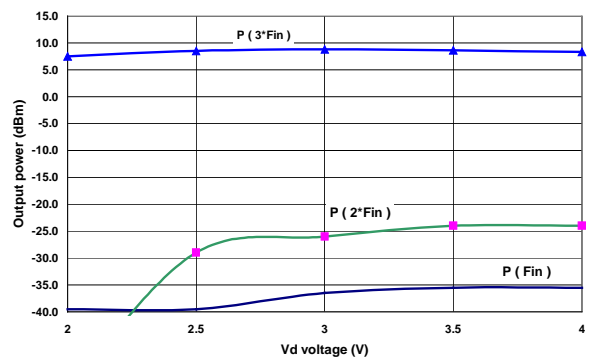
Pout versus Fin @ Pin=14 dBm & Vd=3V



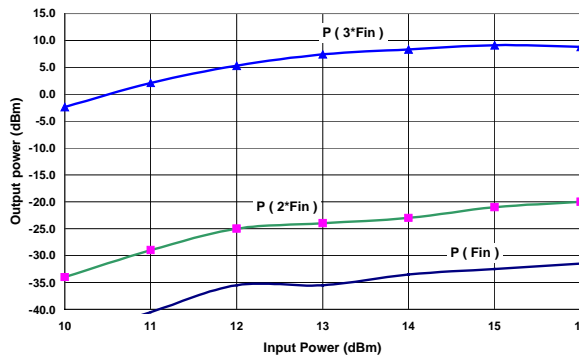
Pout versus Fin @ Pin=14 dBm & Vd=3.5V



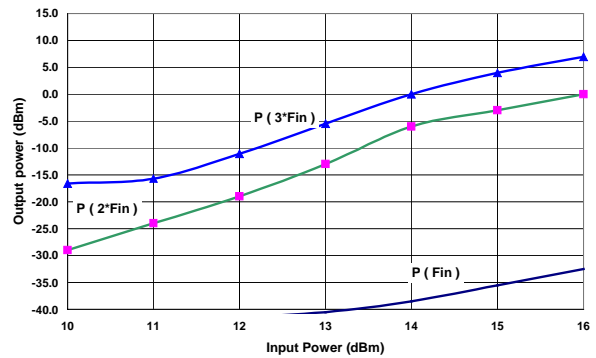
Pout versus Vd @ Pin=14dBm & Fin=13GHz



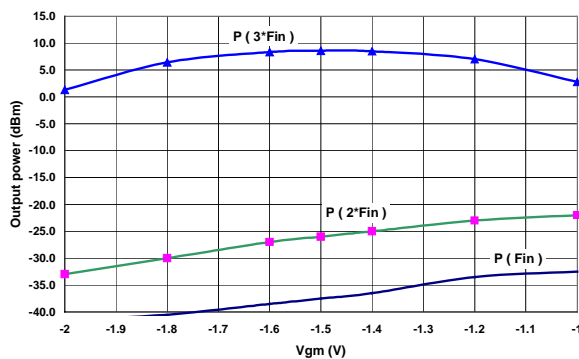
Pout versus Vd @ Pin=14dBm & Fin=12GHz



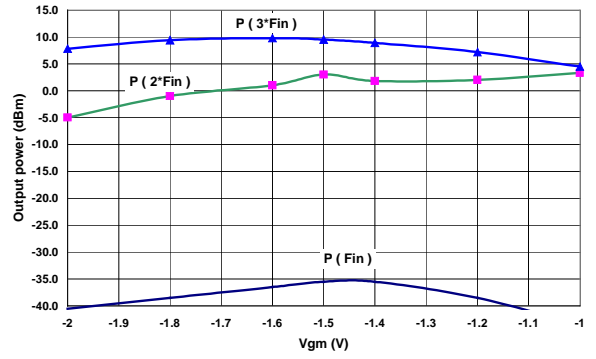
Pout versus Pin @ Fin=12GHz & Vd=3V



Pout versus Pin @ Fin=14GHz & Vd=4V

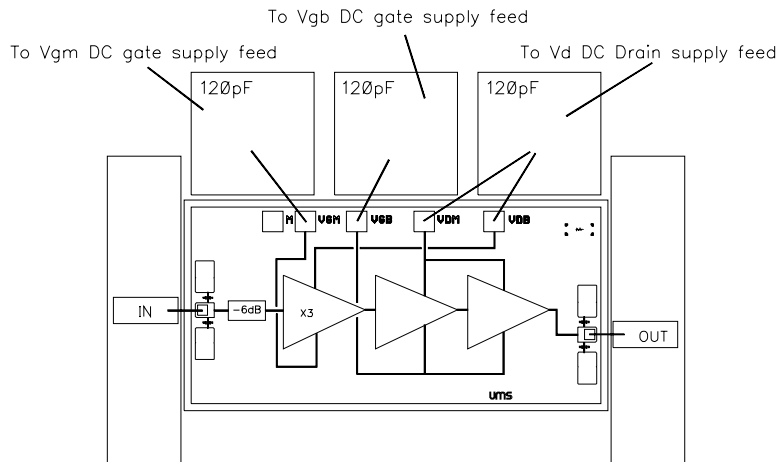


Pout versus Vgm @ Fin=12GHz & Vd=3V

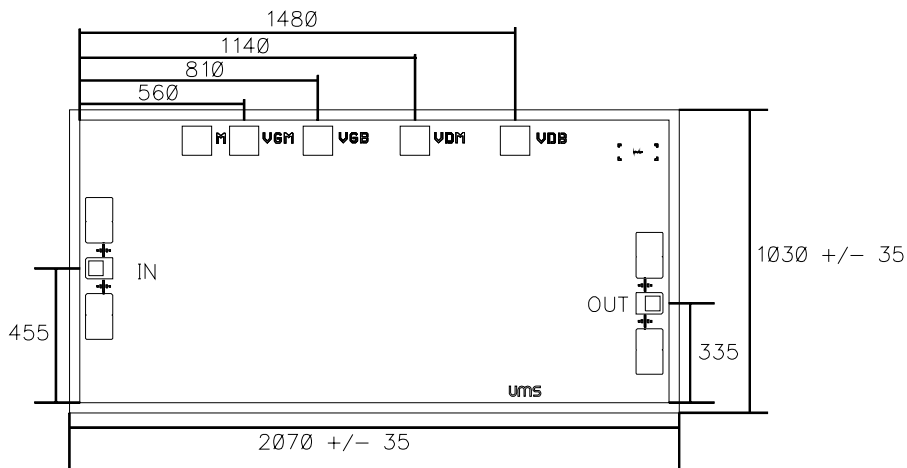


Pout versus Vgm @ Fin=13GHz & Vd=3V

Chip Assembly and Mechanical Data



Note : Supply feed should be capacitively bypassed. 25µm diameter gold wire is to be preferred
Bond Pad:100 x 100 µm².



Bonding pad positions.

(Chip thickness : 100µm. All dimensions are in micrometers)

Ordering Information

Chip form : CHX1094-99F/00

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